

This diagram shows a cross-sectional view of a semiconductor device. A substrate 310 is at the base. A gate stack 320 is formed on the substrate. A first gate stack 330 is formed on the gate stack 320. A second gate stack 332 is formed on the first gate stack 330. A second gate stack 334 is formed on the second gate stack 332. A second gate stack 338 is formed on the second gate stack 334. A second gate stack 340 is formed on the second gate stack 338. A second gate stack 360 is formed on the second gate stack 340. A second gate stack 334 is formed on the second gate stack 332. A second gate stack 338 is formed on the second gate stack 334. A second gate stack 340 is formed on the second gate stack 338. A second gate stack 360 is formed on the second gate stack 340.